

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Tony P. Chiang et al.
Assignee: Angstrom Systems, Inc.
Title: Varying Conductance Out Of A Process Region To Control Gas Flux In An ALD Reactor
Application No.: 10/027,592 Filing Date: 19 December 2001
Examiner: Unknown Group Art Unit: Unknown
Docket No.: M-11466-8C US

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BOX NON-FEE AMENDMENT
COMMISSIONER FOR PATENTS
Washington, D. C. 20231

PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination of this application, please enter the following amendments:

I. IN THE CLAIMS

A. Please replace the pending claims with the following like-numbered claims:

1. (Amended) A method comprising the acts of:

supplying an atomic layer deposition process gas to a process chamber, wherein a gas flow conductance is defined for gas exiting the chamber; and
varying a flux of the deposition process gas to a substrate in the process chamber by varying the conductance;
wherein varying the conductance comprises varying a restriction through which gas exits the chamber.

LAW OFFICES OF
SKJERVEN MORRILL
MACPHERSON LLP
25 METRO DRIVE
SUITE 700
SAN JOSE, CA 95110
(408) 453-9200
FAX (408) 453-7979